

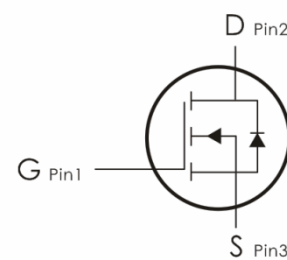
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=40V, I_D=120A, R_{DS(ON)}<4m\Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current ¹	120	A
	Continuous Drain Current-TC=100 $^\circ\text{C}$	85	
	Pulsed Drain Current ²	330	
E_{AS}	Single Pulse Avalanche Energy ³	1080	mJ
P_D	Power Dissipation ⁴	130	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case ¹	1.15	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ¹	---	

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	40	45	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=40V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	1.2	1.9	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance ²	$V_{GS}=10V, I_D=20A$	---	3.2	4	m Ω
		$V_{GS}=4.5V, I_D=10A$	---	5.5	7	
G_{FS}	Forward Transconductance	$V_{DS}=10V, I_D=20A$	26	---	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1\text{MHz}$	---	5400	---	pF
C_{oss}	Output Capacitance		---	970	---	
C_{rss}	Reverse Transfer Capacitance		---	380	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V, I_D=2A,$ $R_{GEN}=3\ \Omega, V_{GS}=10V$	---	15	---	ns
t_r	Rise Time		---	18	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	52	---	ns
t_f	Fall Time		---	23	---	ns
Q_g	Total Gate Charge	$V_{GS}=10V, V_{DS}=20V,$ $I_D=20A$	---	75	---	nC
Q_{gs}	Gate-Source Charge		---	10.5	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	17	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage ²	$V_{GS}=0V, I_S=40A$	---	---	1.2	V

Ls	Diode Forward Current (Note 2)	---	---	---	120	A
Trr	Reverse Recovery Time	T _J = 25°C, I _F = 40A di/dt = 100A/μs ^(Note3)	---	42	---	NS
Qrr	Reverse Recovery Charge		---	45	---	NC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : T_J=25°C, V_{DD}=20V, V_G=10V, L=1mH, R_g=25Ω, I_{AS}=46.5A

Typical Characteristics: (T_c=25°C unless otherwise noted)

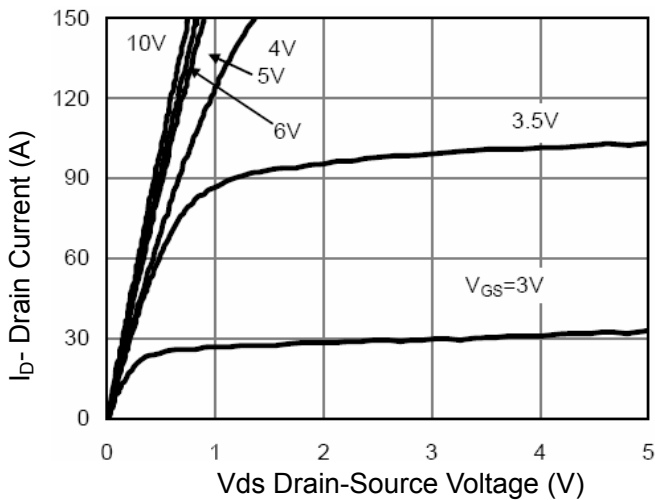


Figure 1 Output Characteristics

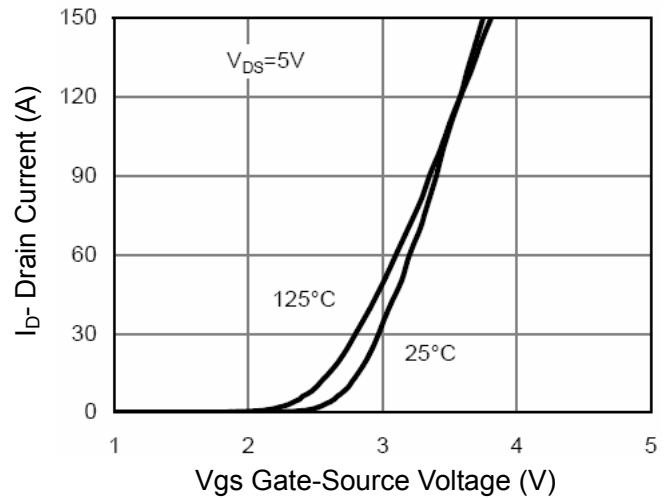


Figure 2 Transfer Characteristics

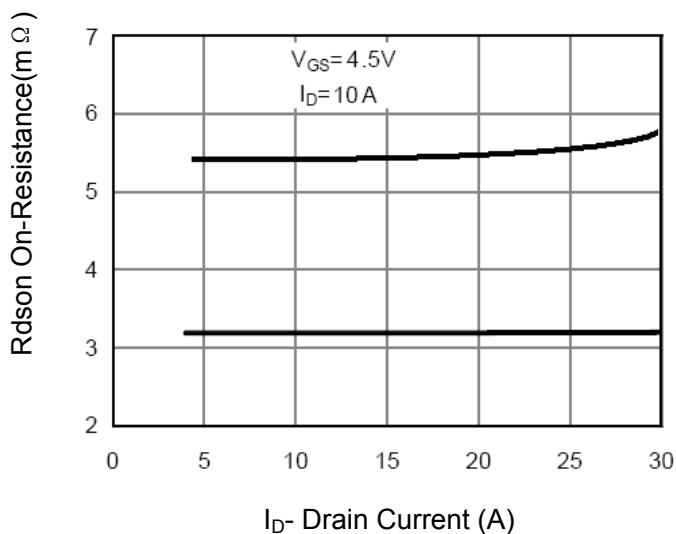


Figure 3 Rdson- Drain Current

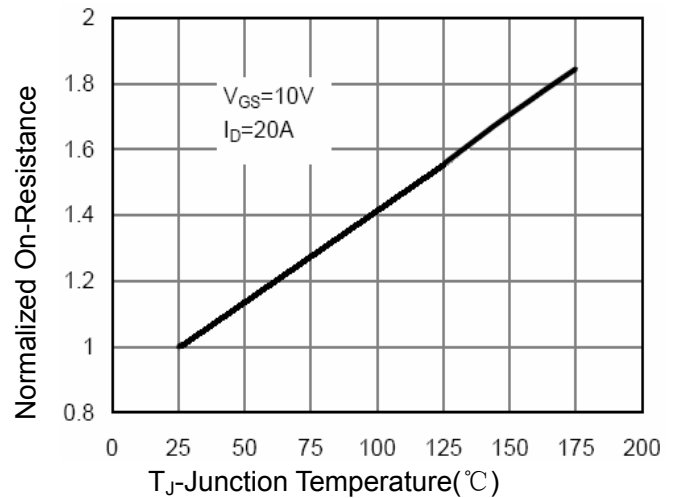


Figure 4 Rdson-Junction Temperature

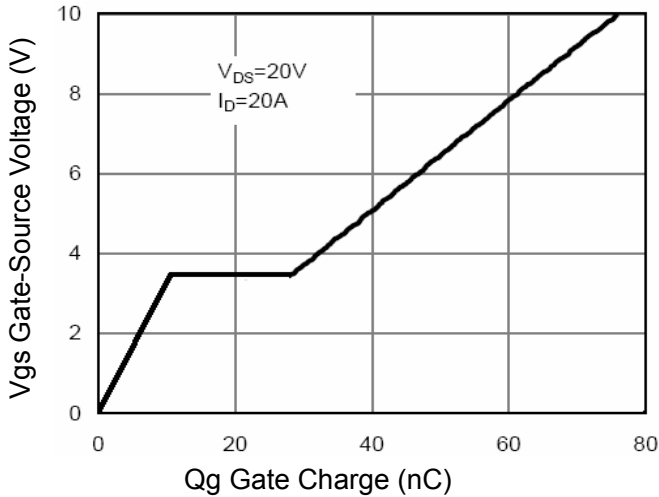


Figure 5 Gate Charge

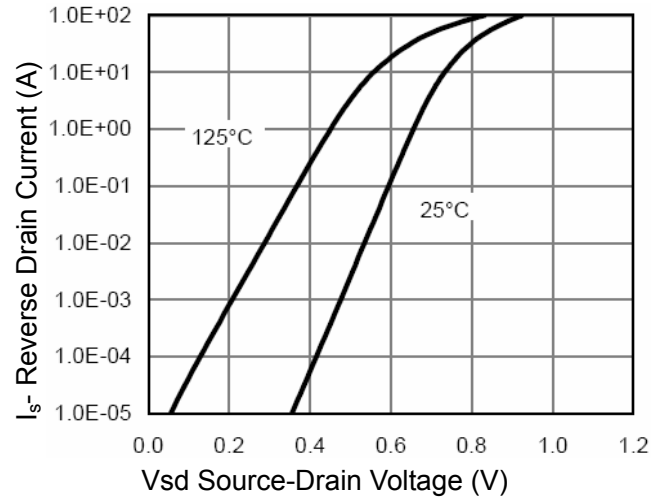


Figure 6 Source- Drain Diode Forward

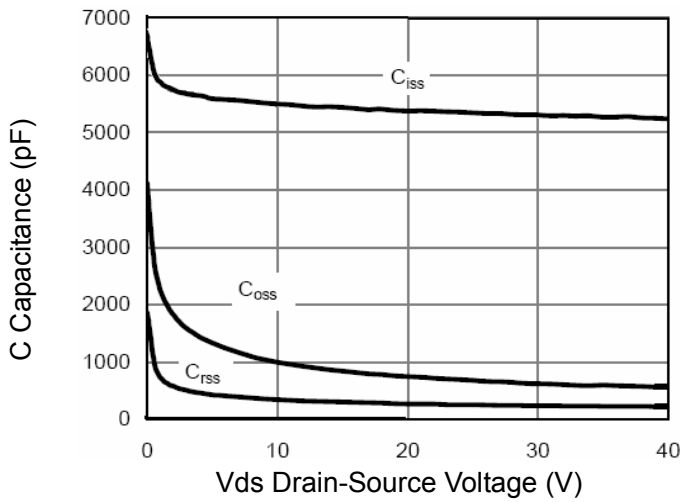


Figure 7 Capacitance vs Vds

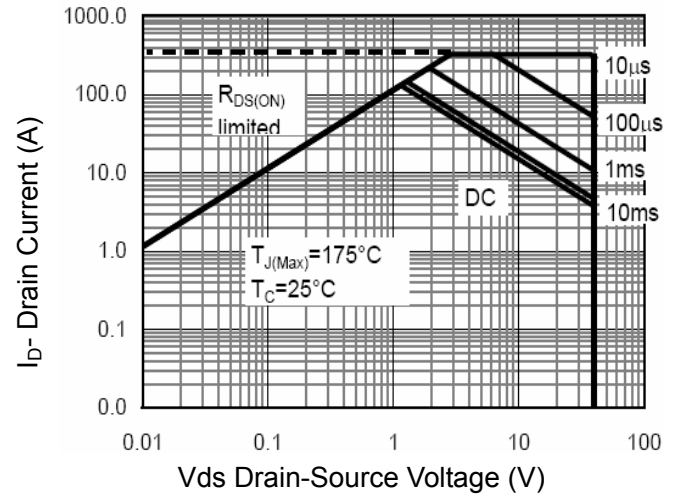


Figure 8 Safe Operation Area

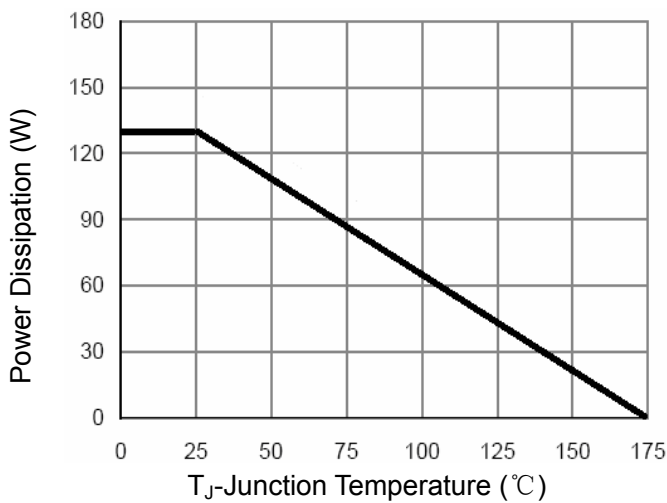


Figure 9 Power De-rating

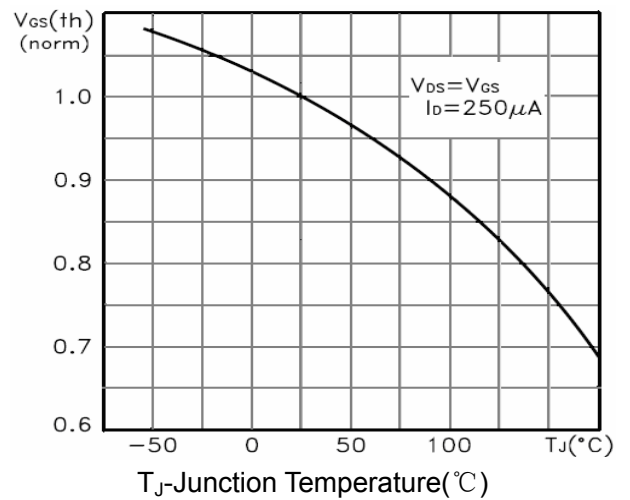


Figure 10 VGS(th) vs Junction Temperature

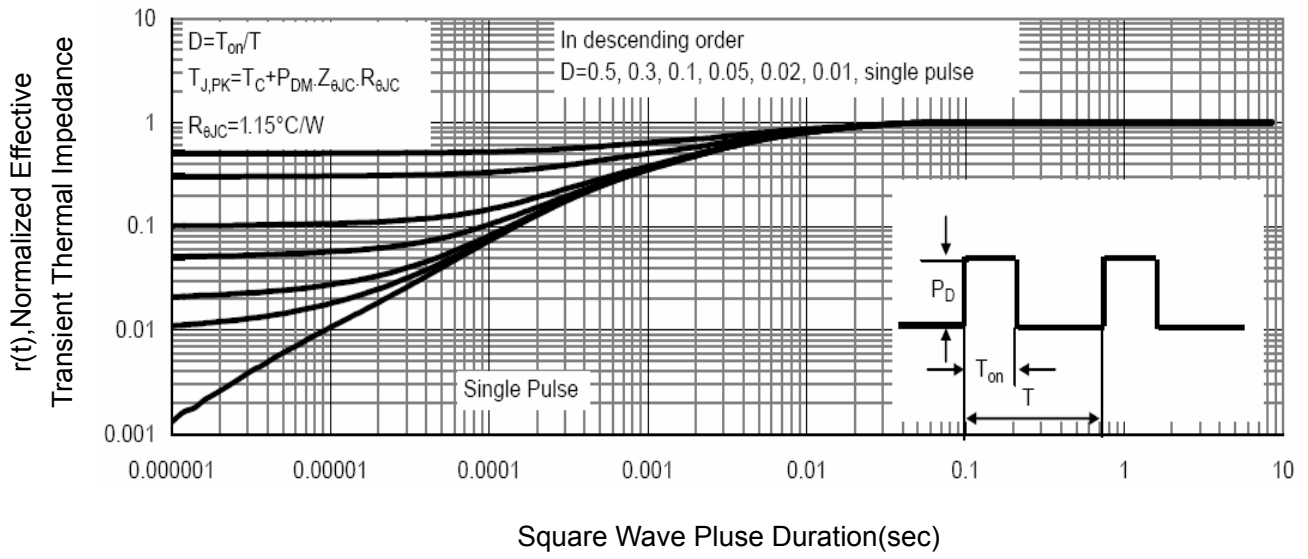


Figure 11 Normalized Maximum Transient Thermal Impedance



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